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(54) **THREE-DIMENSIONAL MEMORY DEVICE INCLUDING A MID-STACK SOURCE LAYER AND METHODS FOR FORMING THE SAME**

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(57) **ABSTRACT**

A memory device includes a first-tier alternating stack of first insulating layers and first electrically conductive layers, a source layer overlying the first-tier alternating stack, a second-tier alternating stack of second insulating layers and second electrically conductive layers overlying the source layer, a memory opening vertically extending through the first-tier alternating stack, the source layer, and the second-tier alternating stack, and a memory opening fill structure located in the memory opening. The memory opening fill structure includes a vertical semiconductor channel that extends through the first-tier alternating stack, the source layer, and the second-tier alternating stack. The vertical semiconductor channel has sidewall in contact with the source layer.